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Date:

October 30, 2002

16

Fax No.:

571.273.1473

Subject:

U.S. Patent Application Serial No. 10/602,072

FROM

Name

David M. Longo, Reg. No. 53,235

Phone No.: 202-408-4489

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DML @ MD 749

Pages (incl. this)

Our File No.:

04329.2470-01

Confirmation Copy to Follow: No

Message:

Further to our conversation earlier today, we attach a copy of the Preliminary Amendment filed on June 24, 2003.

Please verify that you now have all pages of the Preliminary Amendment. Thank you.

If there is a problem with this transmission, notify fax room at (202) 408-4174 or the sender at the number above.

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PATENT Customer No. 22,852 Attorney Docket No. 04329.2470-01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re	Application of:)
Shoji SETA, et al.) Group Art Unit: Not Yet Assigned
Cont.	of Application No.: 09/739,905) Examiner: Not Yet Assigned
Filed:	Herewith	
For:	DRY ETCHING METHOD AND SEMICONDUCTOR DEVICE MANUFACTURING METHOD	
P.O. I	nissioner for Patents Box 1450 undria; VA22313-1450	
Sir:		\

PRELIMINARY AMENDMENT

Prior to the examination of the above application, please amend this application as follows:

IN THE ABSTRACT:

Please replace the current Abstract with the Substitute Abstract attached on a separate page. The full text of the Abstract in clean form is as follows:

--A dry etching method comprises sequentially laminating a first insulating layer containing carbon and a second insulating layer containing carbon on a substrate, patterning the second insulating layer to form a mask; forming grooves in the first insulating layer by etching the first insulating layer with the second insulating layer used as a mask such that each of the grooves has a side surface and a bottom surface in the first insulating layer; and removing the

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